

VOLTAGE RANGE: 20 - 100V

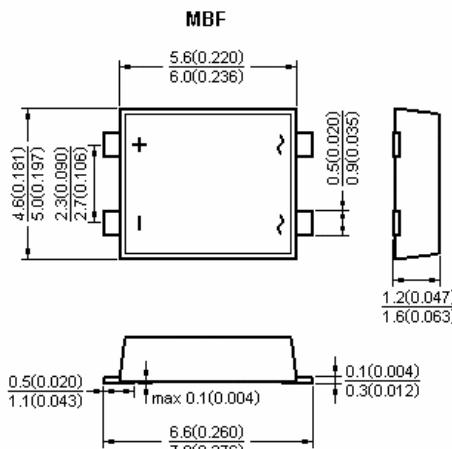
CURRENT: 1.0 A

Features

- Lowprofilepackage
 - Idealforautomatedplacement
 - Ultrafast reverserecovery time
 - Lowpowerlosses, highefficiency
 - Lowforwardvoltagedrop
 - Highsurgecapability
 - High temperaturesoldering!
- 260 °C/10 secondsat terminals

Mechanical Data

- Case:MBFmoldedplasticbodyover Schottkybarrierchips



Dimensions in millimeters and (inches)

Maximum Ratings and Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

	Symbol	KMB12F	KMB14F	KMB16F	KMB18F	KMB110F	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	20	40	60	80	100	V
Maximum RMS voltage	V_{RMS}	14	28	42	56	70	V
Maximum DC blocking voltage	V_{DC}	20	40	60	80	100	V
Maximum average forward rectified current 0.2×0.2"(5.0×5.0mm)copper pad area	$I_{F(AV)}$				1.0		A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load	I_{FSM}				30		A
Maximum instantaneous forward voltage at 1.0A	V_F	0.50	0.55	0.70	0.85		V
Maximum DC reverse current $T_A = 25^\circ\text{C}$ at Rated DC blocking voltage $T_A = 100^\circ\text{C}$	I_R			0.5	20		mA
Typical Junction Capacitance at 4.0V,1.0MHz	C_J		250		125		pF
Typical Thermal resistance (Note1)	$R_{\theta JA}$ $R_{\theta JL}$			85	20		°C/W
Operating junction temperature range	T_J			-55 to +125			°C
Storage temperature range	T_{STG}			- 55 to +150			°C

Note: 1.Thermal resistance from junction to ambient and from junction to lead P.C.B.mounted on 0.2×0.2"(5.0×5.0mm)copper pad areas.



SUNMATE

Fig.1 Forward Current Derating Curve

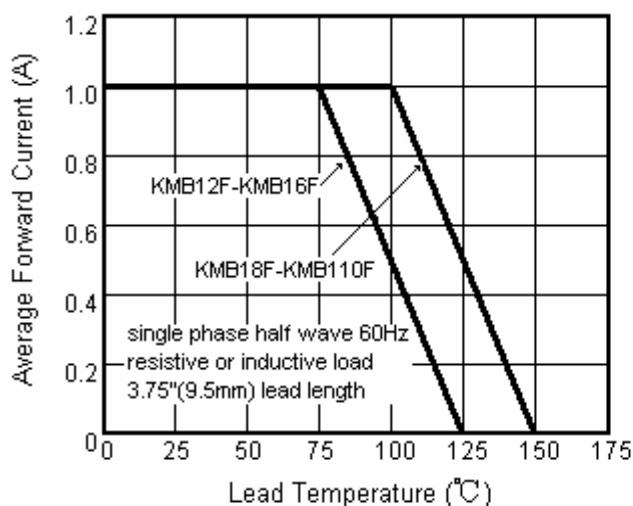


Fig.3 Typical Instantaneous Forward Characteristics

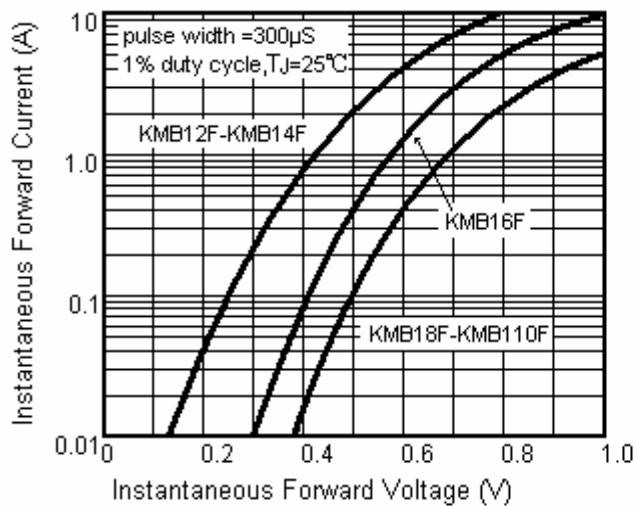


Fig.5 Typical Junction Capacitance

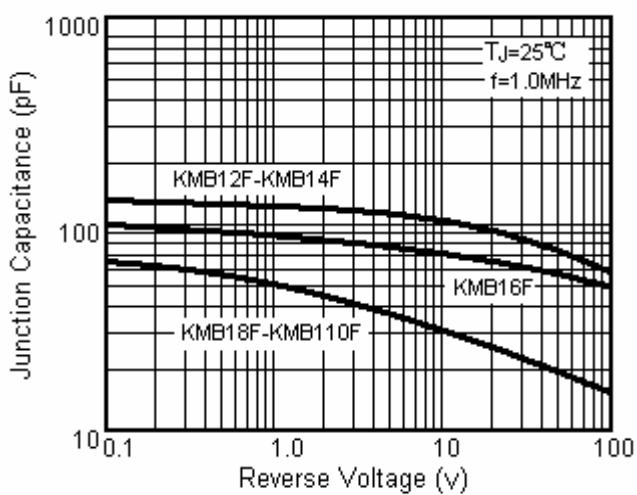


Fig.2 Maximum Non-Repetitive Peak Forward Surge Current

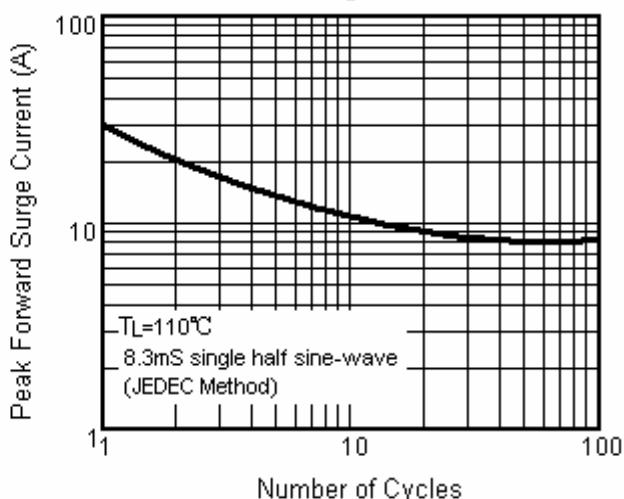


Fig.4A Typical Reverse Characteristics

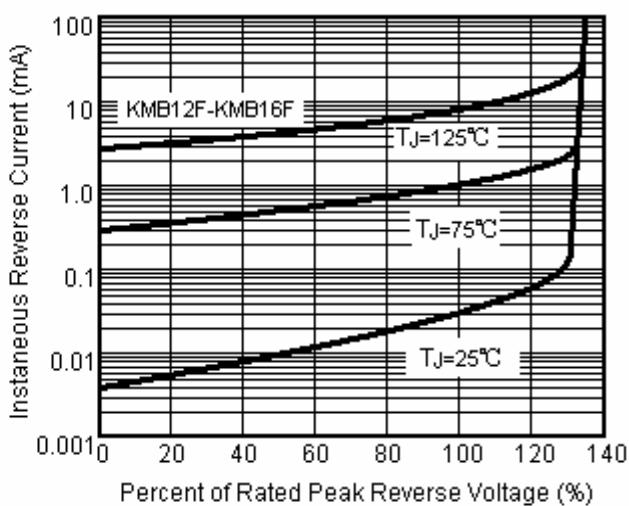


Fig.4B Typical Reverse Characteristics

